## BUSSMANN SERIES

# STS521XXXBXXX TVS Diode ESD suppressor



#### **Product features**

- Compact package size 0.063" x 0.032" (1.6 mm x 0.8 mm)
- · Protects one bi-directional I/O line
- · Low clamping voltage
- Meets moisture sensitivity level (MSL) 3
- Molding compound flammability rating: UL 94V-0
- · Termination finish: Tin

#### **Applications**

- · Cellular handsets and accessories
- Microprocessor based equipment
- · Portable electronics
- · Notebooks, desktops, and servers
- · Portable instrumentation
- Peripherals
- · Digital cameras

## Environmental compliance and general specifications

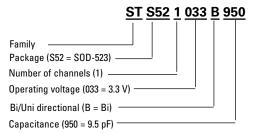
- IEC61000-4-2 (ESD)
  - Up to ±30 kV (air)
  - Up to ±30 kV (contact)
- IEC61000-4-5 (Lightning) Up to 20 A (8/20 μs)







#### Ordering part number



#### Pin out/functional diagram



SOD-523



Pin Configuration



**Absolute maximum ratings** (+25 °C, RH=45%-75%, unless otherwise noted)

Parameter	Symbol	Value					Unit
		STS521050BL90	STS521050B250	STS521050B750	STS521033B950	STS521050B331	
Peak pulse power dissipation on 8/20 µs waveform	P <sub>pp</sub>	20	40	100	60	350	W
ESD per IEC 61000-4-2 (Air)	$V_{\rm ESD}$	+/-15	+/-20	+/-30	+/-30	+/-25	kV
ESD per IEC 61000-4-2 (Contact)		+/-8	+/-15	+/-30	+/-25	+/-20	
Lead soldering temperature	T <sub>L</sub>	+260 (10 seconds)				°C	
Operating junction temperature range	T <sub>J</sub>	-55 to +125			°C		
Storage temperature range	T <sub>STG</sub>		-55 to +150			°C	

#### **Electrical characteristics**

(+25 °C)

#### STS521050BL90

Parameter	Test condition	Minimum	Typical	Maximum	Symbol (Units)
Reverse working voltage	-	-	-	5.0	V <sub>RWM</sub> (V)
Reverse breakdown voltage	I <sub>T</sub> = 1 mA	6.0	-	-	V <sub>BR</sub> (V)
Reverse leakage current	$V_{RWM} = 5 V$	-	-	1	I <sub>R</sub> (μΑ)
Clamping voltage	$I_{pp} = 1 A,$ $t_{p} = 8/20 \mu s$	-	-	13	V <sub>c</sub> (V)
Junction capacitance	$V_{RWM} = 0V, f = 1 MHz$	-	0.9	1.5	C <sub>J</sub> (pF)

S	TS52	10	50	В2	50	
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Parameter	Test condition	Minimum	Typical	Maximum	Symbol (Units)
Reverse working voltage	-	-	-	5.0	V <sub>RWM</sub> (V)
Reverse breakdown voltage	I <sub>T</sub> = 1 mA	6.0	-	-	V <sub>BR</sub> (V)
Reverse holding voltage	-	-	-	0.15	V <sub>R</sub> (V)
Reverse leakage current	V <sub>RWM</sub> = 5 V	-	-	2	I <sub>R</sub> (μΑ)
Clamping voltage	I <sub>pp =</sub> 2 A, t <sub>p</sub> = 8/20 μs	-	12.5	13.5	V <sub>c</sub> (V)
Junction capacitance	$V_{RWM} = 0V$ , $f = 1 MHz$	-	2.5	4	C <sub>J</sub> (pF)

### STS521XXXBXXX TVS Diode ESD suppressor

STS521	050B750
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Parameter	Test condition	Minimum	Typical	Maximum	Symbol (Units)
Reverse working voltage	-	-	-	5.0	V <sub>RWM</sub> (V)
Reverse breakdown voltage	I <sub>T</sub> = 1 mA	5.5	-	-	V <sub>BR</sub> (V)
Reverse holding voltage	$I_{H} = 50 \text{ mA}$	5.5	-		V <sub>R</sub> (V)
Reverse leakage current	V <sub>RWM</sub> = 5 V	-	-	0.1	I <sub>R</sub> (μΑ)
Clamping voltage	I <sub>pp =</sub> 1 A, t <sub>o</sub> = 8/20 μs	-	9	10	V <sub>c</sub> (V)
	$I_{pp} = 5 \text{ A},$ $t_p = 8/20  \mu\text{s}$		13	15.5	V <sub>c</sub> (V)
Junction capacitance	$V_{RWM} = 0V, f = 1 MHz$	-	7.5	15	C <sub>J</sub> (pF)

STS521033B950 Parameter	Test condition	Minimum	Typical	Maximum	Symbol (Units)
Reverse working voltage	-	-	-	3.3	V <sub>RWM</sub> (V)
Reverse breakdown voltage	I <sub>T</sub> = 1 mA	3.6	-	-	V <sub>BR</sub> (V)
Reverse holding voltage	I <sub>H</sub> = 50 mA	3.5	-	-	V <sub>R</sub> (V)
Reverse leakage current	V <sub>RWM</sub> = 3.3 V	-	-	1	I <sub>R</sub> (μΑ)
Clamping voltage	$I_{pp} = 1 \text{ A},$ $t_p = 8/20  \mu \text{s}$	-	6	8	V <sub>c</sub> (V)
	$I_{pp} = 4.5 \text{ A},$ $t_p = 8/20  \mu\text{s}$	-	9	12	V <sub>c</sub> (V)
Junction capacitance	V <sub>RWM</sub> = 0V, f = 1 MHz	=	9.5	15	C <sub>J</sub> (pF)

STS521050B331 Parameter	Test condition	Minimum	Typical	Maximum	Symbol (Units)
Reverse working voltage	-	-	-	5.0	V <sub>RWM</sub> (V)
Reverse breakdown voltage	I <sub>T</sub> = 1 mA	5.5	-	-	V <sub>BR</sub> (V)
Reverse leakage current	V <sub>RWM</sub> = 5 V	-	-	1	I <sub>R</sub> (μΑ)
Clamping voltage	$I_{pp} = 1 A,$ $t_p = 8/20 \ \mu s$	-	7.5	9.0	V <sub>c</sub> (V)
	$I_{pp} = 20 \text{ A},$ $t_p = 8/20  \mu\text{s}$		12	18	V <sub>c</sub> (V)

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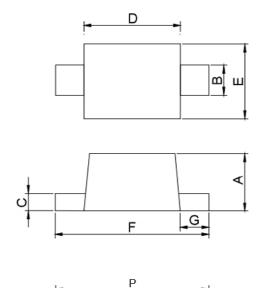
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 $C_J$  (pF)

 $V_{RWM} = 0V, f = 1 MHz$ 

Junction capacitance

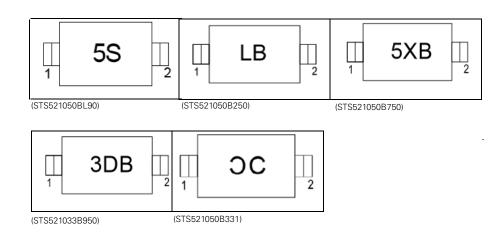
#### Mechanical parameters, pad layout- mm/inches



**Land Pattern** 

Millimeters		Inc	hes	
Dimension	Minimum	Maximum	Minimum	Maximum
A	0.50	0.70	0.020	0.028
В	0.25	0.35	0.010	0.014
С	0.07	0.20	0.0028	0.0079
D	1.10	1.30	0.043	0.051
E	0.70	0.90	0.028	0.035
F	1.50	1.70	0.059	0.067
G	0.15	0.25	0.006	0.010
P1	0.40		0.01	6
P	1.80		0.07	2

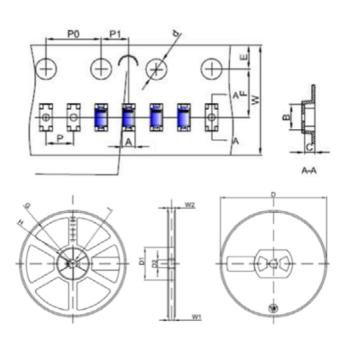
#### Part marking



#### Packaging information mm/inches

Drawing not to scale.

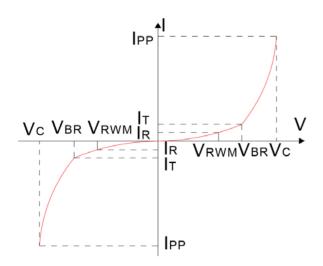
Supplied in tape and reel packaging, 5,000 parts per 7" diameter reel (EIA-481 compliant)



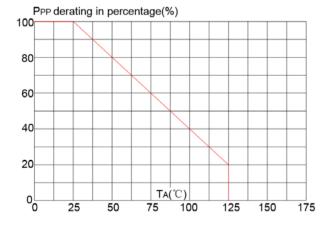
Comple of	Millimeter	Inches
Symbol	Тур.	Тур.
Α	0.90	0.035
В	1.94	0.076
С	0.73	0.029
d	Ф1.50	Ф0.059
E	1.75	0.069
F	3.50	0.138
P0	4.00	0.157
Р	2.00	0.079
P1	2.00	0.079
W	8.00	0.315
D	Ф178	Ф7.008
D1	54.40	2.142
D2	13.00	0.512
G	R78.00	R3.071
Н	R25.60	R1.008
ı	R6.50	R0.256
W1	9.50	0.374
W2	12.30	0.484

#### Ratings and V-I characteristic curves (+25 °C unless otherwise noted)

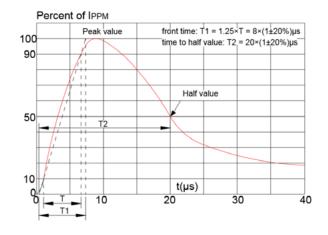
#### V- I curve characteristics (Bi-directional)



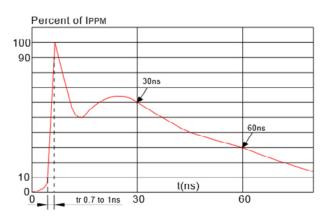
#### Pulse derating curve



#### Pulse waveform (8/20 µs)



#### **ESD** waveform



#### Solder reflow profile

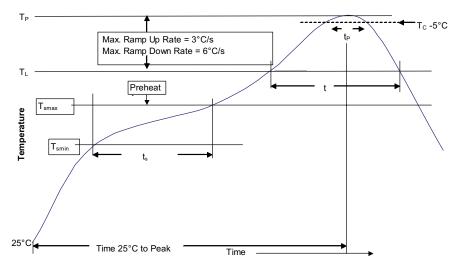


Table 1 - Standard SnPb solder (T<sub>C</sub>)

Package thickness	Volume mm3 <350	Volume mm3 ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2 - Lead (Pb) free solder (T<sub>C</sub>)

Package thickness	Volume mm³ <350	Volume mm³ 350 - 2000	Volume mm³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 – 2.5 mm	260 °C	250 °C	245 °C
>2.5 mm	250 °C	245 °C	245 °C

#### Reference J-STD-020

Profile feature	Standard SnPb solder	Lead (Pb) free solder
Preheat and soak • Temperature min. (T <sub>smin</sub> )	100 °C	150 °C
• Temperature max. (T <sub>smax</sub> )	150 °C	200 °C
• Time (T <sub>smin</sub> to T <sub>smax</sub> ) (t <sub>s</sub> )	60-120 seconds	60-120 seconds
Ramp up rate T <sub>L</sub> to T <sub>p</sub>	3 °C/ second max.	3 °C/ second max.
Liquidous temperature ( $T_L$ ) Time ( $t_L$ ) maintained above $T_L$	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body temperature (Tp)*	Table 1	Table 2
Time (t <sub>p</sub> )* within 5 °C of the specified classification temperature (T <sub>C</sub> )	20 seconds*	30 seconds*
Ramp-down rate (T <sub>p</sub> to T <sub>L</sub> )	6 °C/ second max.	6 °C/ second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

<sup>\*</sup> Tolerance for peak profile temperature  $(T_p)$  is defined as a supplier minimum and a user maximum.

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